	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
1	BRS	L2	2	(partial$4 or select$5) near (bond$4 or join$4) with wafer with oxide and (dic$4 or cut$5 or separat$4 or singulat$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/25 01:34			
2	BRS	L3	98	(partial$4 or select$5) with (bond$4 or join$4) with wafer with oxide and (dic$4 or cut$5 or separat$4 or singulat$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/25 01:20			
3	BRS	L4	16	(partial$4 or select$5) near3 (bond$4 or join$4) with wafer with oxide and (dic$4 or cut$5 or separat$4 or singulat$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/25 01:17			
4	BRS	L5	31	(partial$4 or select$5) with (bond$4 or join$4) with wafer with oxide and (dic$4 or cut$5 or separat$4 or singulat$4) and plan$7 with surface	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/25 01:21			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
5	BRS	L7	22	("3332137" | "3475664" | "3579055" | "3623219" | "3832247" | "5091331" | "5169472" | "5183769" | "5385632").PN. OR ("5654226").URPN.	US-PGPUB; USPAT; USOCR	2005/11/25 01:28			
6	BRS	L9	100	(partial$4 or select$5 or segment$4) with (bond$4 or join$4) with oxide with wafer and (dic$4 or cut$5 or separat$4 or singulat$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/25 01:44			
7	BRS	L10	31	(partial$4 or select$5 or segment$4) with (bond$4 or join$4) with oxide and releas$ with (device or circuit) and wafer and (dic$4 or cut$5 or separat$4 or singulat$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/25 01:51			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
8	BRS	L11	43	(bond$4 or join$4) with oxide with wafer and releas$ with (device or circuit) with (dic$4 or cut$5 or separat$4 or singulat$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/25 01:51			
9	BRS	L12	16	("438"/464).ccls. and (bond$4 or join$4) with wafer with oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/25 01:59			
10	BRS	L15	62	("438"/$).ccls. and (bond$4 or join$4) near wafer near oxide and (dic$4 or cut$5 or separat$4 or singulat$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/25 02:00			
11	BRS	L16	62	("438"/$).ccls. and (partial$4 or select$5 or segment$4)with (bond$4 or join$4) with wafer with oxide and (dic$4 or cut$5 or separat$4 or singulat$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/25 02:03			